

ABSTRACT OF THE DISCLOSURE

The present invention relates to a sense amplifier for reading a memory cell, comprising a read node linked directly or indirectly to the memory cell, a first active branch connected to the read node, comprising means for supplying a read current at the read node, and a data output linked to one node of the first active branch at which a voltage representative of the conductivity state of the memory cell appears. According to the present invention, the sense amplifier comprises a second active branch connected to the read node, comprising means for supplying, at the read node, a current that is added to the current supplied by the first active branch, such that the voltage representative of the conductivity state of the memory cell remains substantially stable upon a current draw at the read node. Application particularly to reading non-volatile FLASH and EEPROM type memory cells.

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